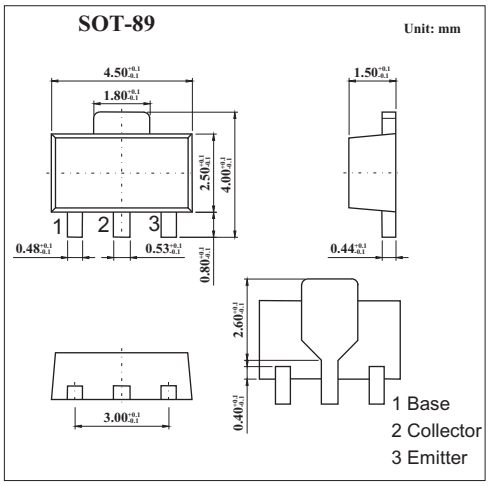
Epitaxial Planar PNP Transistor

KTA1666

Features

Collector Power dissipation: P_C=500mW

Collector Current -Continuous: I_C=-2A



Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-2	A
Collector Power dissipation	P_C	500	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-1mA, I_E=0	-50			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-50			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-5.0			V
Collector cut-off current	I_{CBO}	V_{CB}= -50 V , I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -5 V , I_B=0			-0.1	μA
DC current gain	h_{FE1}	V_{CE}=-2V, I_C= -0.5A	70		240	
	h_{FE2}	V_{CE}=-2V, I_C= -1.5A	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-1A, I_B= 50mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= -1A, I_B= 50mA			-1.2	V
Transition frequency	f_T	V_{CE}= -2V, I_C=-0.5A		120		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		40		pF

h_{FE} Classification

Marking	WO	WY
Rank	O	Y
Range	70 140	120 240